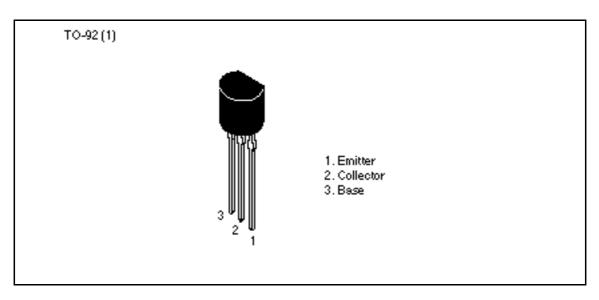
## Silicon PNP Epitaxial

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#### Application

- Low frequency low noise amplifier
- Complementary pair with 2SC2545, 2SC2546 and 2SC2547

#### Outline





### Absolute Maximum Ratings (Ta = $25^{\circ}$ C)

Item	Symbol	2SA1083	2SA1084	2SA1085	Unit
Collector to base voltage	V <sub>CBO</sub>	-60	-90	-120	V
Collector to emitter voltage	V <sub>CEO</sub>	-60	-90	-120	V
Emitter to base voltage	$V_{\text{EBO}}$	-5	-5	-5	V
Collector current	I <sub>c</sub>	-100	-100	-100	mA
Emitter current	Ι <sub>Ε</sub>	100	100	100	mA
Collector power dissipation	P <sub>c</sub>	400	400	400	mW
Junction temperature	Tj	150	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	-55 to +150	°C

#### **Electrical Characteristics** (Ta = 25°C)

		2SA1083		2SA1084 2SA		2SA1	SA1085					
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	-60	_	_	-90	_	_	-120	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60	—	—	-90	—	_	-120	—	_	V	$I_{c} = -1 \text{ mA},$ $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	_	-5	—	_	V	$I_{\rm E} = -10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I <sub>CBO</sub>	—	—	-0.1	—	—	-0.1	—	—	-0.1	μA	$V_{CB} = -50 \text{ V}, \text{ I}_{E} = 0$
Emitter cutoff current	$I_{\text{EBO}}$	_		-0.1	—	_	-0.1	—	_	-0.1	μA	$V_{EB} = -2 V, I_{C} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	250	_	800	250	_	800	250	_	800		$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	-0.2	_	_	-0.2	_	_	-0.2	V	$I_{\rm C} = -10 \text{ mA},$ $I_{\rm B} = -1 \text{ mA}$
Base to emitter voltage	$V_{BE}$	_	-0.6	_	_	-0.6	_	_	-0.6	_	V	$V_{CE} = -12 \text{ V},$ $I_C = -2 \text{ mA}$
Gain bandwidth product	f <sub>T</sub>	_	90	_	_	90	_	_	90	_	MHz	$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector output capacitance	Cob	_	3.5	_	_	3.5	_	—	3.5	_	рF	$V_{CB} = -10 \text{ V}, \text{ I}_{E} = 0,$ f = 1 MHz
Noise voltage reffered to input	e <sub>n</sub>		0.5	_	_	0.5	_	_	0.5	_	nV/ Hz	$V_{CE} = -6V,$ $I_{c} = -10 \text{ mA},$ f = 1  kHz, $R_{g} = 0, f = 1\text{ Hz}$

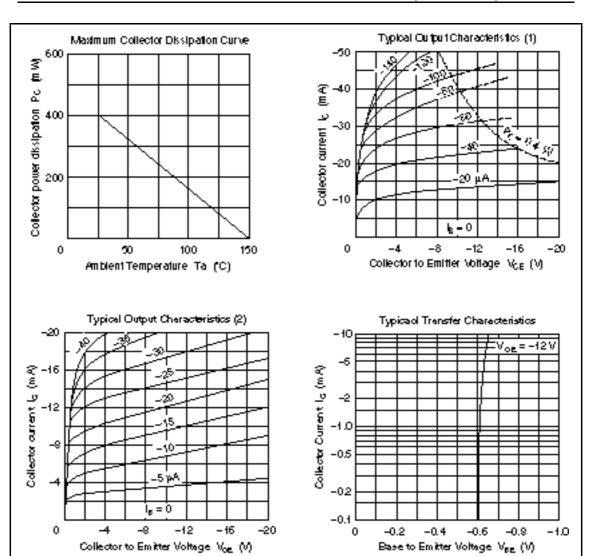
Note: 1. The 2SA1083, 2SA1084 and 2SA1085 are grouped by  $h_{\mbox{\tiny FE}}$  as follows.

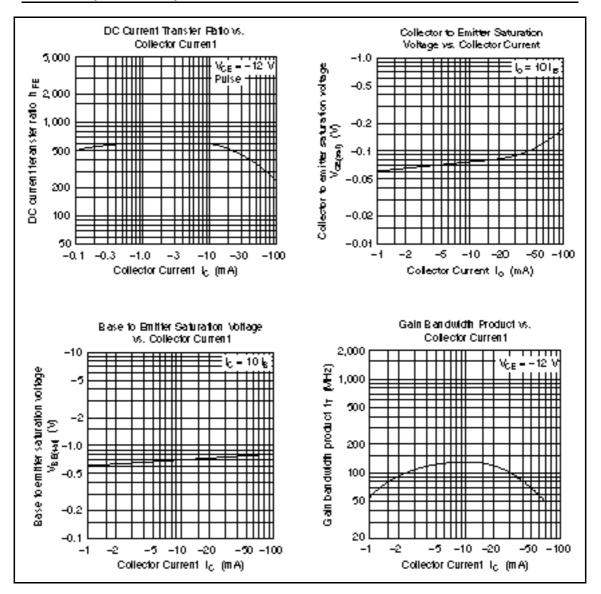
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250 to 500 400 to 800

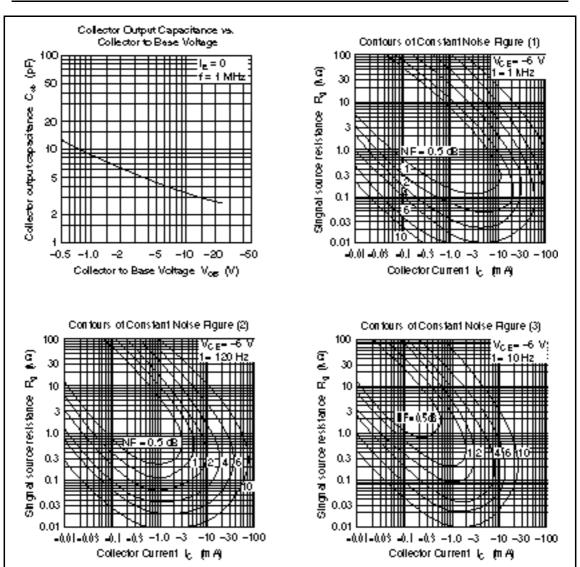
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